

# Si photodiodes

S1337 series

# For UV to IR, precision photometry

These Si photodiodes have sensitivity in the UV to near IR range. They are suitable for low-light-level detection in analysis and the like.

#### **Features**

- Arr High UV sensitivity: QE 75% ( $\lambda$ =200 nm)
- **Low capacitance**

#### Applications

- Analytical equipment
- Optical measurement equipment

#### **Structure / Absolute maximum ratings**

				Effective	Absolute maximum ratings				
Type no.	Window material	Package	Photosensitive area size	photosensitive area	Reverse voltage VR max	Operating temperature Topr	Storage temperature Tstg		
		(mm)	(mm)	(mm <sup>2</sup> )	(V)	(°C)	(°C)		
S1337-16BQ*	Quartz	2.7 × 15	1.1 × 5.9	5.9			-20 to +80		
S1337-16BR	Resin potting	2./ × 15	1.1 × 5.9						
S1337-33BQ*	Quartz	6 × 7.6	2.4 × 2.4	5.7					
S1337-33BR	Resin potting	0 × 7.0	2.4 × 2.4			-20 to +60			
S1337-66BQ*	Quartz	8.9 × 10.1	5.8 × 5.8	33	5	-20 10 +60			
S1337-66BR	Resin potting	0.9 × 10.1	3.6 × 3.6						
S1337-1010BQ*	Quartz	15 × 16.5	10 × 10	100					
S1337-1010BR	Resin potting	15 × 10.5	10 × 10	100					
S1337-21*	Unsealed	25.5 × 25.5	18 × 18	324		0 to +60	0 to +80		

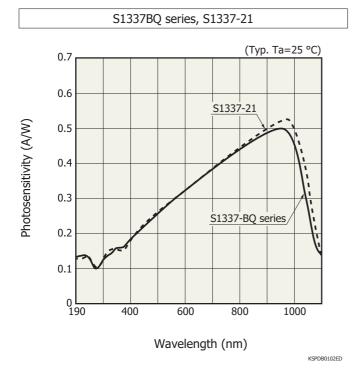
<sup>\*</sup> Refer to "Precautions against UV light exposure."

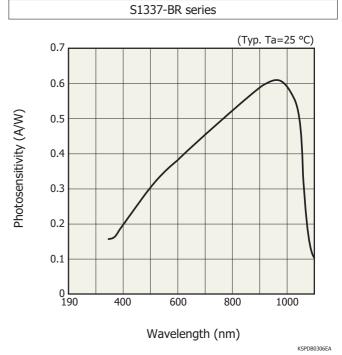
Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

### **➡** Electrical and optical characteristics (Typ. Ta=25 °C, unless otherwise noted)

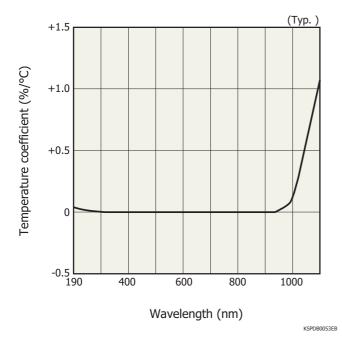
Туре по.	Spectral response range $\lambda$	Peak sensitivity wavelength λp	Photosensitivity S (A/W)				Short circuit current Isc 100 lx		Dark	of	VR=0 V	Terminal capacitance Ct	Rsh		Noise equivalent power	
				200	nm He-Ne GaAs laser LED		Min.	Тур.	Max.	TCID	RL=1 k $\Omega$	f=10 kHz	VR=10 mV		NEP	
			λр	Min.	Tim	633	930							Min.	Тур.	
	(nm)	(nm)		I*   1.	Тур.	nm	nm	(µA)	(µA)	(pA)	(times/°C)	(µs)	(pF)	(GΩ)	(GΩ)	(W/Hz <sup>1/2</sup> )
S1337-16BQ	190 to 1100	960	0.5	0.10	0.12	0.33	0.5	4.0	5.3	50		0.2	65	0.2	0.6	$1.0 \times 10^{-14}$
S1337-16BR	340 to 1100		0.62	-	-	0.4	0.6	4.4	6.2	30		0.2				$8.4 \times 10^{-15}$
S1337-33BQ	190 to 1100		0.5	0.10	0.12	0.33	0.5	4.0	5.0	30		0.2	65	0.3	1	$8.1 \times 10^{-15}$
S1337-33BR	340 to 1100		0.62	-	-	0.4	0.6	4.4	6.2	30						$6.5 \times 10^{-15}$
S1337-66BQ	190 to 1100		0.5	0.10	0.12	0.33	0.5	20	27	200	1.15	1	380	0.1	0.4	$1.3 \times 10^{-14}$
S1337-66BR	340 to 1100		0.62	-	-	0.4	0.6	22	33							$1.0 \times 10^{-14}$
S1337-1010BQ	190 to 1100		0.5	0.10	0.12	0.33	0.5	65	78			3	1100	0.05	0.2	$1.8 \times 10^{-14}$
S1337-1010BR	340 to 1100		0.62	-	-	0.4	0.6	70	95							1.5 × 10 <sup>-14</sup>
S1337-21	190 to 1100		0.52	0.10	0.13	0.34	0.51	200	250	500		8	4000	0.02	0.1	$2.5 \times 10^{-14}$

#### Spectral response

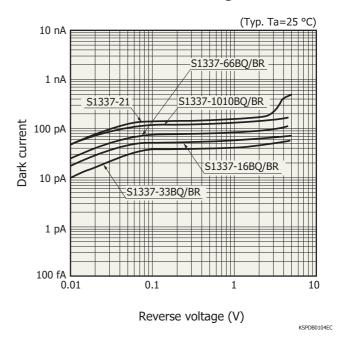




#### **▶** Photosensitivity temperature characteristics

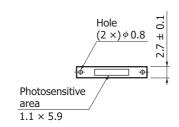


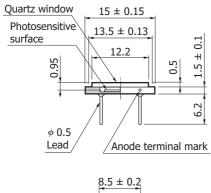
#### **►** Dark current vs. reverse voltage



#### Dimensional outlines (unit: mm)





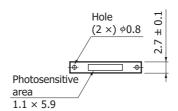




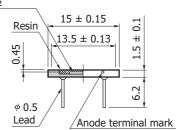
②⊶◄⊸①

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#### S1337-16BR



Photosensitive surface



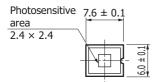


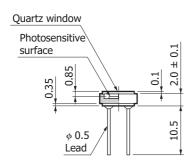
② ○ ★ ○ ①

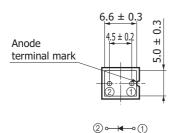
The resin potting may extend a maximum of 0.1 mm above the upper surface of the package.

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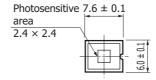
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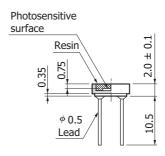


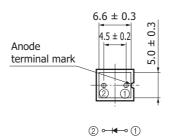




#### S1337-33BR







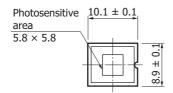
The resin potting may extend a maximum of 0.1 mm above the upper surface of the package.

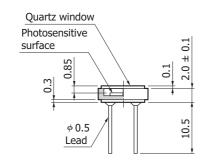
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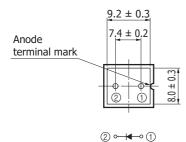


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#### S1337-66BQ

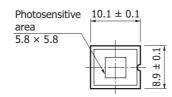


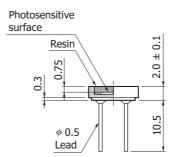


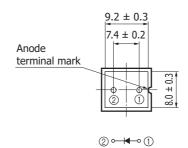


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#### S1337-66BR



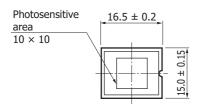


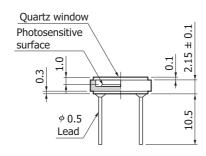


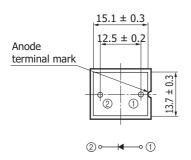
The resin potting may extend a maximum of 0.1 mm above the upper surface of the package.

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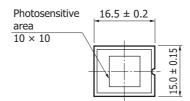
#### S1337-1010BQ

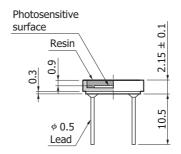


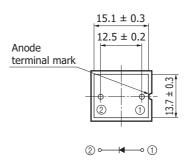




#### S1337-1010BR







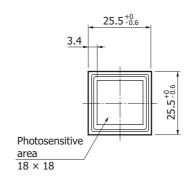
The resin potting may extend a maximum of 0.1 mm above the upper surface of the package.

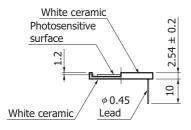
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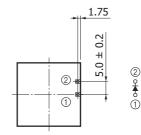


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KSPDA0190EA

#### Precautions against UV light exposure

- · When UV light irradiation is applied, the product characteristics may degrade. Such examples include degradation of the product's UV sensitivity and increase in dark current. This phenomenon varies depending on the irradiation level, irradiation intensity, usage time, and ambient environment and also varies depending on the product model. Before employing the product, we recommend that you check the tolerance under the ultraviolet light environment that the product will be used in.
- Exposure to UV light may cause the characteristics to degrade due to gas released from the resin bonding the product's component materials. As such, we recommend that you avoid applying UV light directly on the resin and apply it on only the inside of the photosensitive area by using an aperture or the like.

#### Si photodiodes

#### S1337 series

#### Related information

www.hamamatsu.com/sp/ssd/doc\_en.html

- Precautions
- · Disclaimer
- · Metal, ceramic, plastic package products
- Technical information
- · Si photodiode/Application circuit examples

Information described in this material is current as of October, 2015.

Product specifications are subject to change without prior notice due to improvements or other reasons. This document has been carefully prepared and the information contained is believed to be accurate. In rare cases, however, there may be inaccuracies such as text errors. Before using these products, always contact us for the delivery specification sheet to check the latest specifications.

The product warranty is valid for one year after delivery and is limited to product repair or replacement for defects discovered and reported to us within that one year period. However, even if within the warranty period we accept absolutely no liability for any loss caused by natural disasters or improper product use. Copying or reprinting the contents described in this material in whole or in part is prohibited without our prior permission.

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